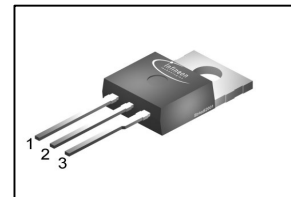


**CoolMOS™ Power Transistor**
**Features**

- New revolutionary high voltage technology
- Extreme dv/dt rated
- High peak current capability
- Qualified according to JEDEC<sup>1)</sup> for target applications
- Pb-free lead plating; RoHS compliant
- Ultra low gate charge
- Ultra low effective capacitances

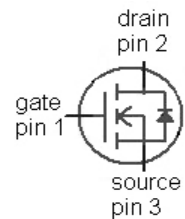
**Product Summary**

|  |     |          |
|--|-----|----------|
| $V_{DS}$                                   | 800 | V        |
| $R_{DS(on)max}$ @ $T_j = 25^\circ\text{C}$ | 0.9 | $\Omega$ |
| $Q_{g,typ}$                                | 31  | nC       |

**PG-TO220-3**

**CoolMOS™ 800V designed for:**

- Industrial application with high DC bulk voltage
- Switching Application ( i.e. active clamp forward )

| Type       | Package    | Marking |
|------------|------------|---------|
| SPP06N80C3 | PG-TO220-3 | 06N80C3 |


**Maximum ratings, at  $T_j=25^\circ\text{C}$ , unless otherwise specified**

| Parameter   | Symbol         | Conditions                             | Value       | Unit             |
|---|----------------|--|-------------|------------------|
| Continuous drain current                                | $I_D$          | $T_C=25^\circ\text{C}$                 | 6           | A                |
|   |                | $T_C=100^\circ\text{C}$                | 3.8         |                  |
| Pulsed drain current <sup>2)</sup>                      | $I_{D,pulse}$  | $T_C=25^\circ\text{C}$                 | 18          |                  |
| Avalanche energy, single pulse                          | $E_{AS}$       | $I_D=1.2\text{ A}, V_{DD}=50\text{ V}$ | 230         | mJ               |
| Avalanche energy, repetitive $t_{AR}$ <sup>2),3)</sup>  | $E_{AR}$       | $I_D=6\text{ A}, V_{DD}=50\text{ V}$   | 0.2         |                  |
| Avalanche current, repetitive $t_{AR}$ <sup>2),3)</sup> | $I_{AR}$       |  | 6           | A                |
| MOSFET dv/dt ruggedness                                 | dv/dt          | $V_{DS}=0\dots640\text{ V}$            | 50          | V/ns             |
| Gate source voltage                                     | $V_{GS}$       | static                                 | $\pm 20$    | V                |
|   |                | AC ( $f>1\text{ Hz}$ )                 | $\pm 30$    |                  |
| Power dissipation                                       | $P_{tot}$      | $T_C=25^\circ\text{C}$                 | 83          | W                |
| Operating and storage temperature                       | $T_j, T_{stg}$ |  | -55 ... 150 | $^\circ\text{C}$ |
| Mounting torque   |                | M3 and M3.5 screws                     | 60          | Ncm              |

**Maximum ratings**, at  $T_j=25\text{ °C}$ , unless otherwise specified

| Parameter                           | Symbol        | Conditions         | Value | Unit |
|-------------------------------------|---------------|--------------------|-------|------|
| Continuous diode forward current    | $I_S$         | $T_C=25\text{ °C}$ | 6     | A    |
| Diode pulse current <sup>2)</sup>   | $I_{S,pulse}$ |                    | 18    |      |
| Reverse diode $dv/dt$ <sup>4)</sup> | $dv/dt$       |                    | 4     | V/ns |

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

**Thermal characteristics**

|   |            |                                      |   |   |     |     |
|---|------------|--------------------------------------|---|---|-----|-----|
| Thermal resistance, junction - case                         | $R_{thJC}$ |                                      | - | - | 1.5 | K/W |
| Thermal resistance, junction - ambient                      | $R_{thJA}$ | leaded                               | - | - | 62  |     |
| Soldering temperature, wave soldering only allowed at leads | $T_{sold}$ | 1.6 mm (0.063 in.) from case for 10s | - | - | 260 | °C  |

**Electrical characteristics**, at  $T_j=25\text{ °C}$ , unless otherwise specified

**Static characteristics**

|                                  |               |   |     |      |     |               |
|----------------------------------|---------------|---|-----|------|-----|---------------|
| Drain-source breakdown voltage   | $V_{(BR)DSS}$ | $V_{GS}=0\text{ V}$ , $I_D=250\text{ }\mu\text{A}$                | 800 | -    | -   | V             |
| Avalanche breakdown voltage      | $V_{(BR)DS}$  | $V_{GS}=0\text{ V}$ , $I_D=6\text{ A}$                            | -   | 870  | -   |               |
| Gate threshold voltage           | $V_{GS(th)}$  | $V_{DS}=V_{GS}$ , $I_D=0.25\text{ mA}$                            | 2.1 | 3    | 3.9 |               |
| Zero gate voltage drain current  | $I_{DSS}$     | $V_{DS}=800\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=25\text{ °C}$  | -   | -    | 10  | $\mu\text{A}$ |
|                                  |               | $V_{DS}=800\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=150\text{ °C}$ | -   | 50   | -   |               |
| Gate-source leakage current      | $I_{GSS}$     | $V_{GS}=20\text{ V}$ , $V_{DS}=0\text{ V}$                        | -   | -    | 100 | nA            |
| Drain-source on-state resistance | $R_{DS(on)}$  | $V_{GS}=10\text{ V}$ , $I_D=3.8\text{ A}$ , $T_j=25\text{ °C}$    | -   | 0.78 | 0.9 | $\Omega$      |
|                                  |               | $V_{GS}=10\text{ V}$ , $I_D=3.8\text{ A}$ , $T_j=150\text{ °C}$   | -   | 2.1  | -   |               |
| Gate resistance                  | $R_G$         | $f=1\text{ MHz}$ , open drain                                     | -   | 1.2  | -   | $\Omega$      |

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

**Dynamic characteristics**

|  |              |   |   |     |   |    |
|--|--------------|---|---|-----|---|----|
| Input capacitance  | $C_{iss}$    | $V_{GS}=0\text{ V}, V_{DS}=100\text{ V},$   | - | 785 | - | pF |
| Output capacitance   | $C_{oss}$    | $f=1\text{ MHz}$  | - | 33  | - |    |
| Effective output capacitance, energy related <sup>5)</sup> | $C_{o(er)}$  | $V_{GS}=0\text{ V}, V_{DS}=0\text{ V}$<br>to 480 V  | - | 26  | - |    |
| Effective output capacitance, time related <sup>6)</sup>   | $C_{o(tr)}$  |   | - | 69  | - |    |
| Turn-on delay time   | $t_{d(on)}$  | $V_{DD}=400\text{ V},$<br>$V_{GS}=0/10\text{ V}, I_D=6\text{ A},$<br>$R_G=15\text{ }\Omega, T_j=25\text{ }^\circ\text{C}$ | - | 25  | - | ns |
| Rise time  | $t_r$        |   | - | 15  | - |    |
| Turn-off delay time  | $t_{d(off)}$ |   | - | 72  | - |    |
| Fall time  | $t_f$        |   | - | 8   | - |    |

**Gate Charge Characteristics**

|                       |               |  |   |     |    |    |
|-----------------------|---------------|--|---|-----|----|----|
| Gate to source charge | $Q_{gs}$      | $V_{DD}=640\text{ V}, I_D=6\text{ A},$<br>$V_{GS}=0\text{ to }10\text{ V}$ | - | 4   | -  | nC |
| Gate to drain charge  | $Q_{gd}$      |  | - | 15  | -  |    |
| Gate charge total     | $Q_g$         |  | - | 31  | 41 |    |
| Gate plateau voltage  | $V_{plateau}$ |  | - | 5.5 | -  | V  |

**Reverse Diode**

|                               |           |   |   |     |     |               |
|-------------------------------|-----------|---|---|-----|-----|---------------|
| Diode forward voltage         | $V_{SD}$  | $V_{GS}=0\text{ V}, I_F=I_S=6\text{ A},$<br>$T_j=25\text{ }^\circ\text{C}$    | - | 1   | 1.2 | V             |
| Reverse recovery time         | $t_{rr}$  | $V_R=400\text{ V}, I_F=I_S=6\text{ A},$<br>$di_F/dt=100\text{ A}/\mu\text{s}$ | - | 520 | -   | ns            |
| Reverse recovery charge       | $Q_{rr}$  |   | - | 5   | -   | $\mu\text{C}$ |
| Peak reverse recovery current | $I_{rrm}$ |   | - | 18  | -   | A             |

<sup>1)</sup> J-STD20 and JESD22

<sup>2)</sup> Pulse width  $t_p$  limited by  $T_{j,max}$

<sup>3)</sup> Repetitive avalanche causes additional power losses that can be calculated as  $P_{AV}=E_{AR} \cdot f$ .

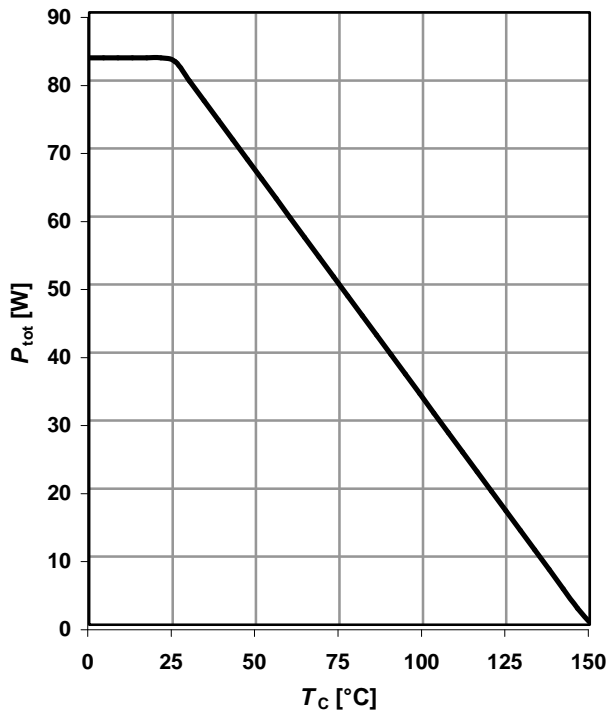
<sup>4)</sup>  $I_{SD}=I_D, di/dt=400\text{ A}/\mu\text{s}, V_{DClink}=400\text{ V}, V_{peak}<V_{(BR)DSS}, T_j<T_{j,max}$ , identical low side and high side switch

<sup>5)</sup>  $C_{o(er)}$  is a fixed capacitance that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .

<sup>6)</sup>  $C_{o(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .

### 1 Power dissipation

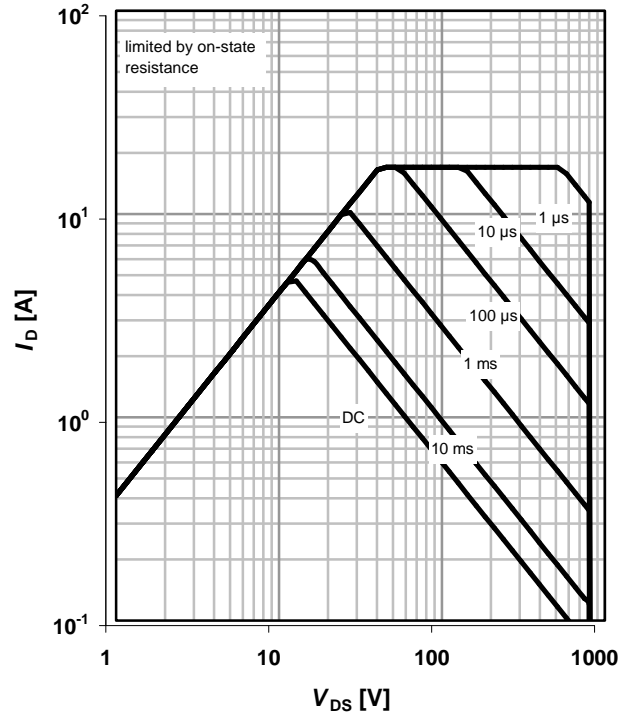
$$P_{tot} = f(T_C)$$



### 2 Safe operating area

$$I_D = f(V_{DS}); T_C = 25^\circ\text{C}; D = 0$$

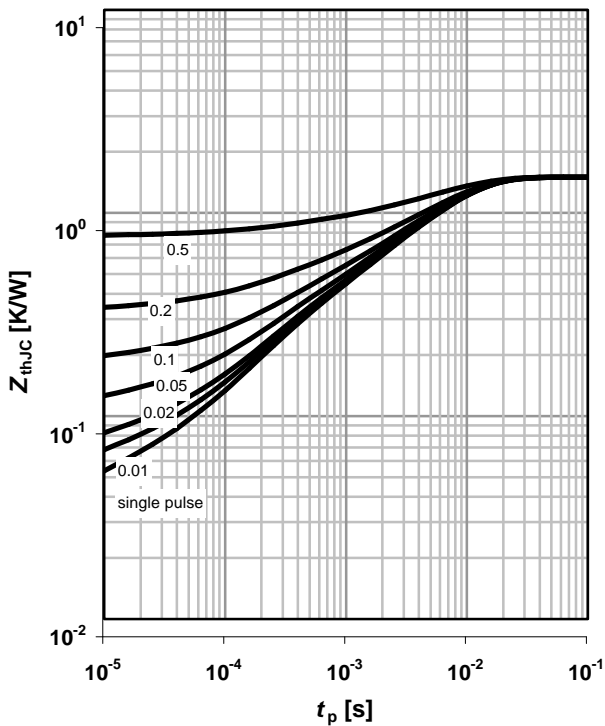
parameter:  $t_p$



### 3 Max. transient thermal impedance

$$Z_{thJC} = f(t_p)$$

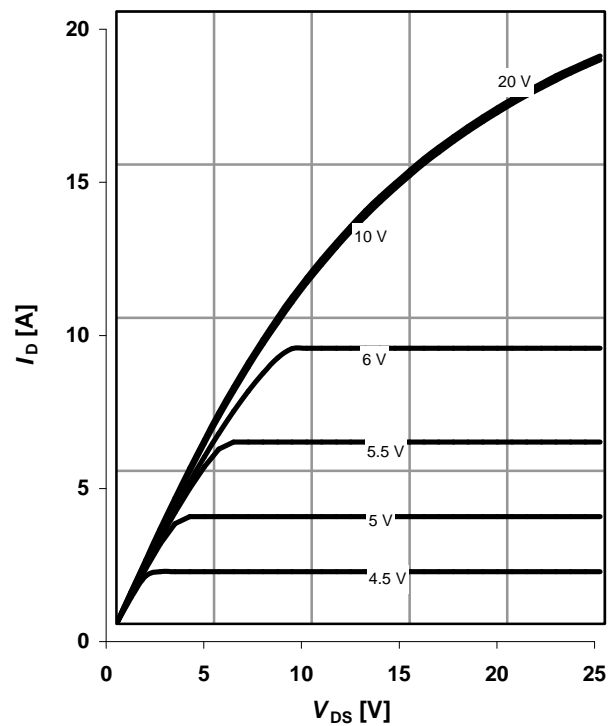
parameter:  $D = t_p / T$



### 4 Typ. output characteristics

$$I_D = f(V_{DS}); T_j = 25^\circ\text{C}; t_p = 10 \mu\text{s}$$

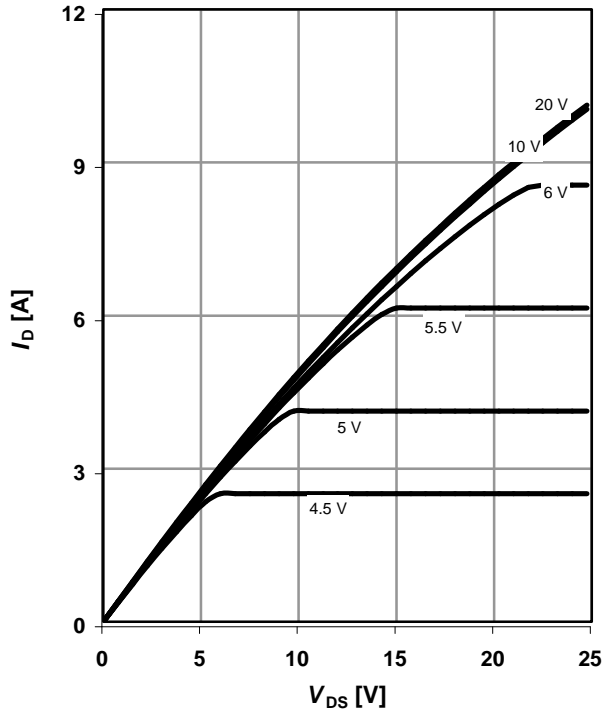
parameter:  $V_{GS}$



**5 Typ. output characteristics**

$I_D=f(V_{DS}); T_j=150\text{ }^\circ\text{C}; t_p=10\text{ }\mu\text{s}$

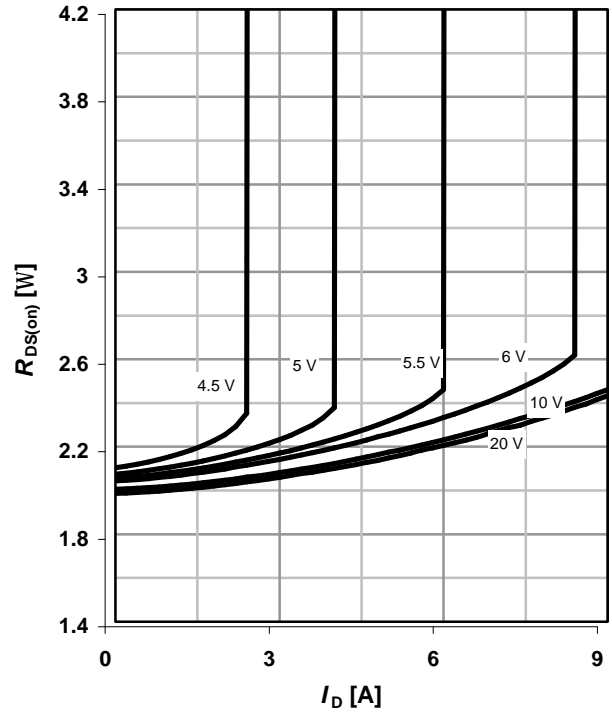
parameter:  $V_{GS}$



**6 Typ. drain-source on-state resistance**

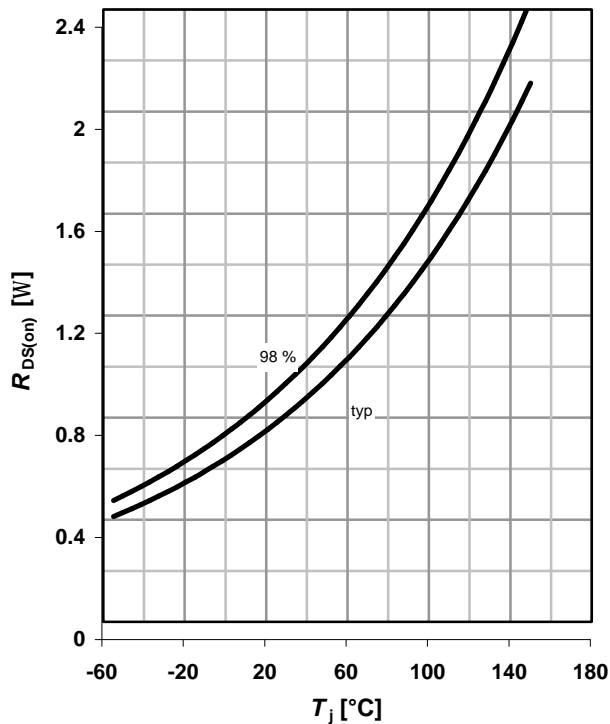
$R_{DS(on)}=f(I_D); T_j=150\text{ }^\circ\text{C}$

parameter:  $V_{GS}$



**7 Drain-source on-state resistance**

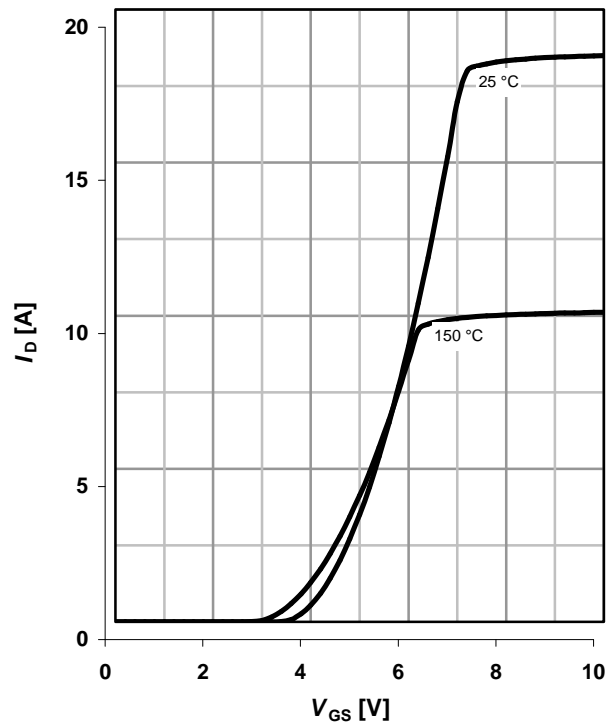
$R_{DS(on)}=f(T_j); I_D=3.8\text{ A}; V_{GS}=10\text{ V}$



**8 Typ. transfer characteristics**

$I_D=f(V_{GS}); |V_{DS}|>2|I_D|R_{DS(on)max}; t_p=10\text{ }\mu\text{s}$

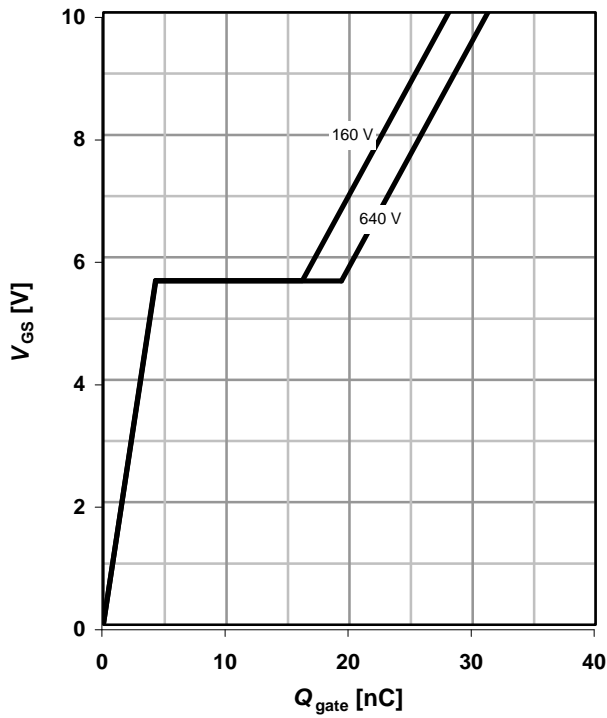
parameter:  $T_j$



**9 Typ. gate charge**

$V_{GS}=f(Q_{gate}); I_D=6\text{ A pulsed}$

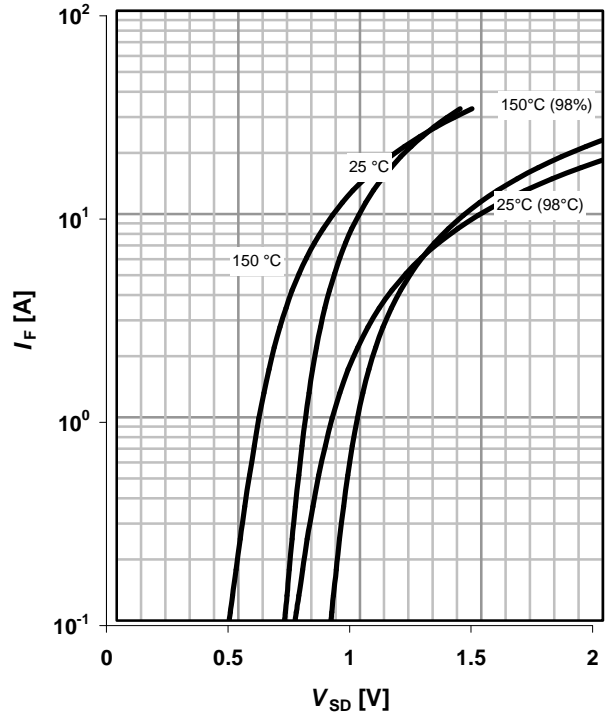
parameter:  $V_{DD}$



**10 Forward characteristics of reverse diode**

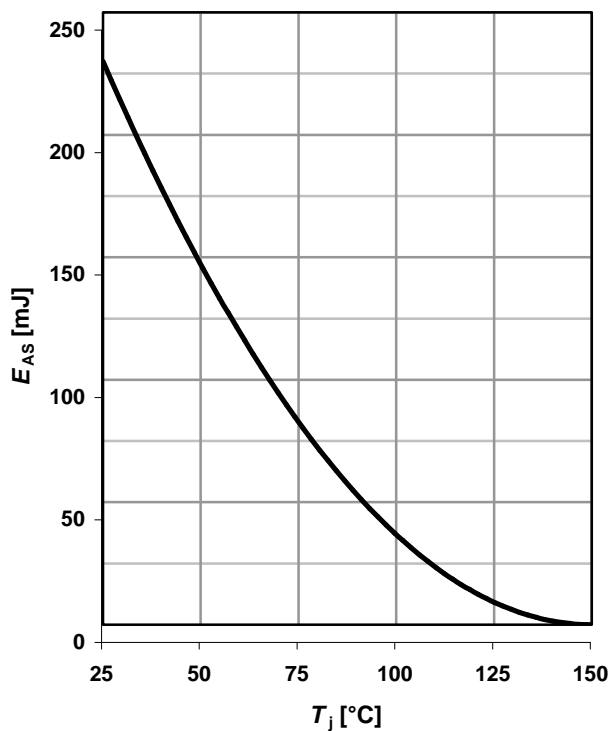
$I_F=f(V_{SD}); t_p=10\ \mu\text{s}$

parameter:  $T_j$



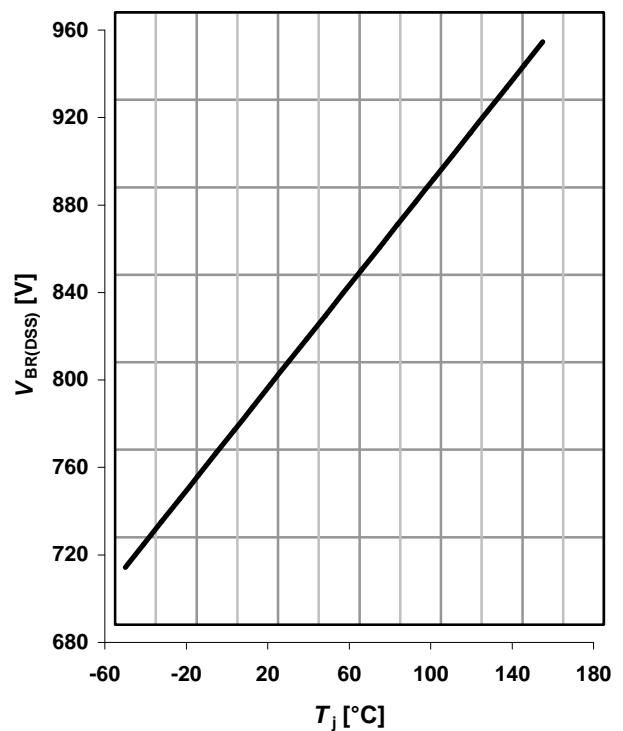
**11 Avalanche energy**

$E_{AS}=f(T_j); I_D=1.2\text{ A}; V_{DD}=50\text{ V}$



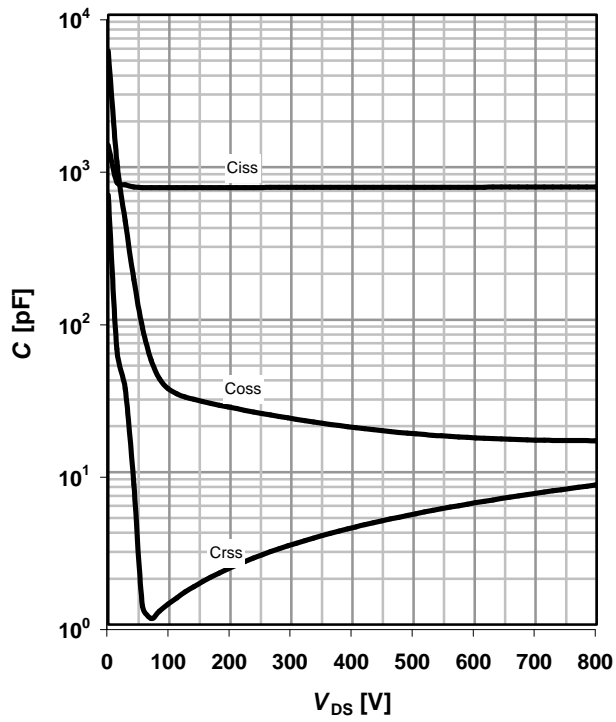
**12 Drain-source breakdown voltage**

$V_{BR(DSS)}=f(T_j); I_D=0.25\text{ mA}$



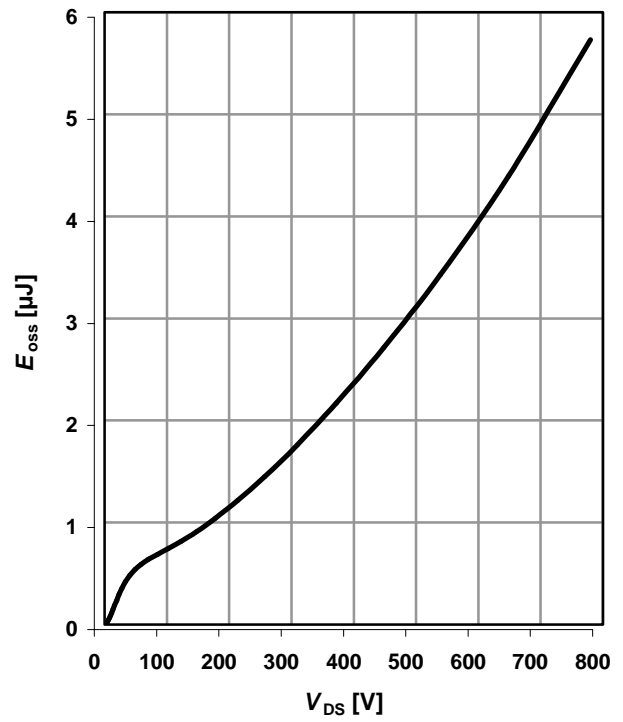
**13 Typ. capacitances**

$C=f(V_{DS}); V_{GS}=0\text{ V}; f=1\text{ MHz}$

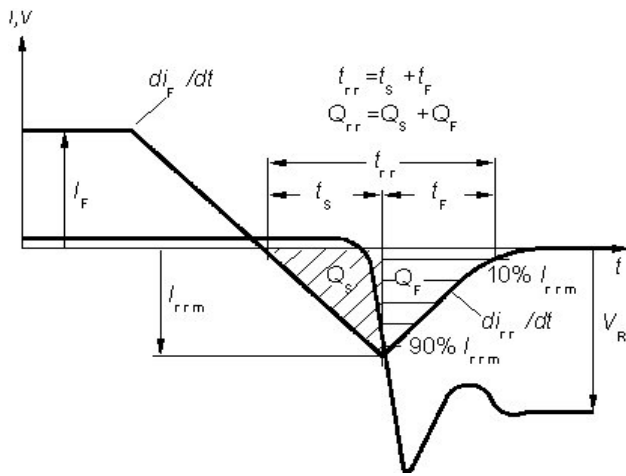


**14 Typ. Coss stored energy**

$E_{oss}=f(V_{DS})$

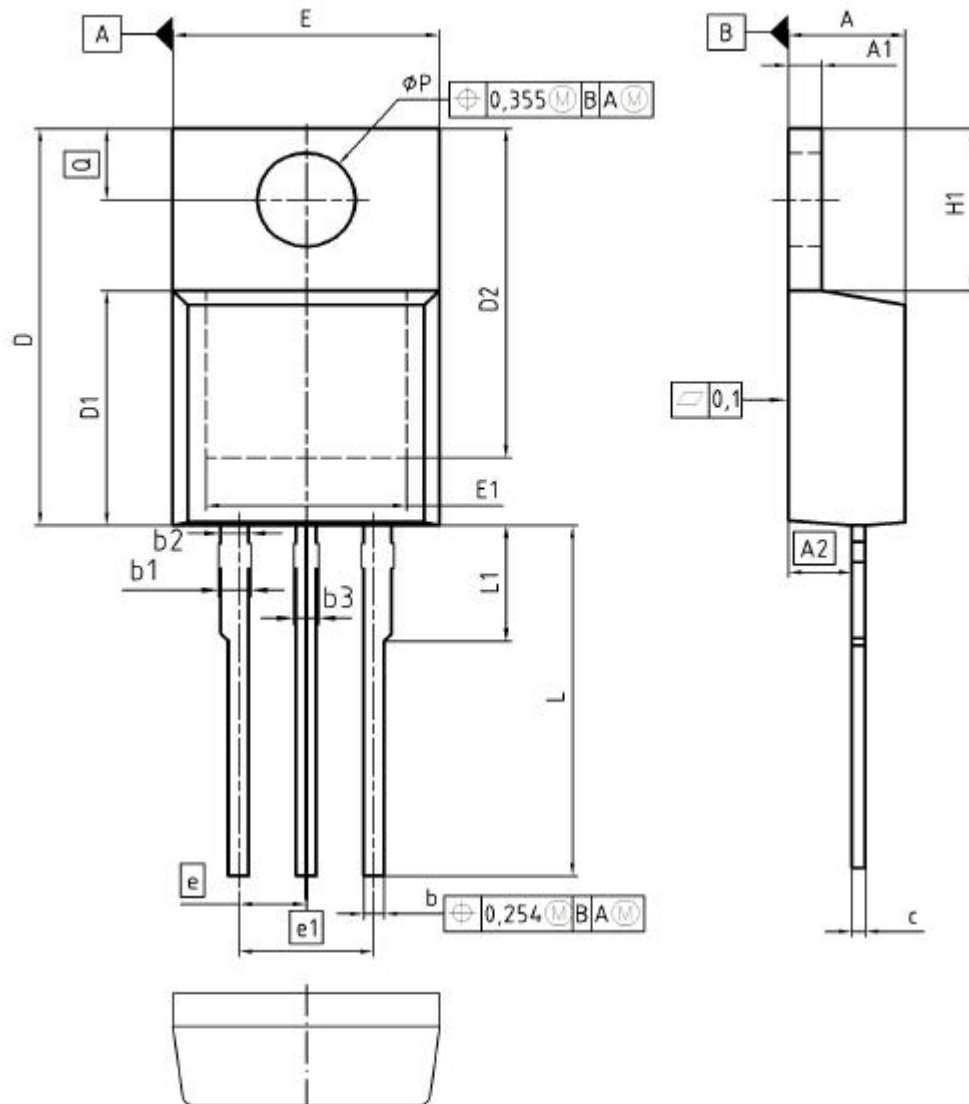


Definition of diode switching characteristics





PG-TO220-3: Outline



| DIM      | MILLIMETERS |       | INCHES |       |
|----------|-------------|-------|--------|-------|
|          | MIN         | MAX   | MIN    | MAX   |
| A        | 4.30        | 4.57  | 0.169  | 0.180 |
| A1       | 1.17        | 1.40  | 0.046  | 0.055 |
| A2       | 2.15        | 2.72  | 0.085  | 0.107 |
| b        | 0.65        | 0.86  | 0.026  | 0.034 |
| b1       | 0.95        | 1.40  | 0.037  | 0.055 |
| b2       | 0.95        | 1.15  | 0.037  | 0.045 |
| b3       | 0.65        | 1.15  | 0.026  | 0.045 |
| c        | 0.33        | 0.60  | 0.013  | 0.024 |
| D        | 14.81       | 15.95 | 0.583  | 0.628 |
| D1       | 8.51        | 9.45  | 0.335  | 0.372 |
| D2       | 12.19       | 13.10 | 0.480  | 0.516 |
| E        | 9.70        | 10.36 | 0.382  | 0.408 |
| E1       | 6.50        | 8.60  | 0.256  | 0.339 |
| e        | 2.54        |       | 0.100  |       |
| e1       | 5.08        |       | 0.200  |       |
| N        | 3           |       | 3      |       |
| H1       | 5.90        | 6.90  | 0.232  | 0.272 |
| L        | 13.00       | 14.00 | 0.512  | 0.551 |
| L1       | -           | 4.80  | -      | 0.189 |
| $\phi P$ | 3.60        | 3.89  | 0.142  | 0.153 |
| Q        | 2.60        | 3.00  | 0.102  | 0.118 |

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